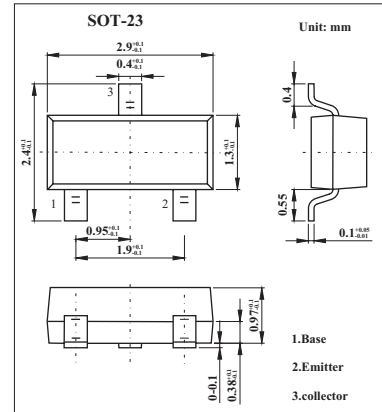


KC807(BC807)

■ Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-45	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current (DC)	I _c	-800	mA
power dissipation	P _d	310	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	V _{CB0}	I _c = -10 μA, V _{BE} = 0	-50			V
Collector-to-emitter breakdown voltage	V _{CE0}	I _c = -10 mA, I _B = 0	-45			V
Emitter-to-base breakdown voltage	V _{EB0}	I _E = -10 μA, I _c = 0	-5			V
Collector cutoff current	I _{CES}	V _{CB} = -25 V, V _{BE} = 0			-100	nA
Emitter cutoff current	I _{EBO}	V _{EB} = -4 V, I _c = 0			-100	nA
DC current gain *	h _{FE}	I _c = -100 mA, V _{CE} = -1 V	100		630	
		I _c = -300 mA, V _{CE} = -1 V	60			
Collector saturation voltage *	V _{CE(sat)}	I _c = -500 mA, I _B = -50 mA			-0.7	V
Base emitter on voltage	V _{BE(on)}	V _{CE} = -1V, I _c = 300mA			-1.2	V
Output Capacitance	C _{ob}	V _{CB} = -10V, f = 1MHz			12	pF
Transition frequency	f _T	I _c = -10 mA, V _{CE} = -5 V, f = 50 MHz		100		MHz

* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ Marking

NO.	KC807-16	KC807-25	KC807-40
Marking	9FA	9FB	9FC
hFE	100~250	160~400	250~630